# Octal Buffer/Line Driver with 3-State Outputs

The MC74ACT241 is an octal buffer and line driver designed to be employed as a memory address driver, clock driver and bus oriented transmitter or receiver which provides improved PC board density.

#### Features

- 3-State Outputs Drive Bus Lines or Buffer Memory Address Registers
- Outputs Source/Sink 24 mA
- TTL Compatible Inputs
- Pb-Free Packages are Available

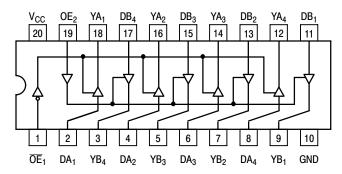


Figure 1. Pinout: 20-Lead Packages Conductors
(Top View)

#### TRUTH TABLE

Inputs		Outputs
OE <sub>1</sub>	D	(Pins 12, 14, 16, 18)
L	L	L
L	Н	Н
Н	Х	Z

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance

#### **TRUTH TABLE**

Inputs		Outputs
OE <sub>2</sub>	D	(Pins 3, 5, 7, 9)
Н	L	L
Н	Н	Н
L	Х	Z

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance



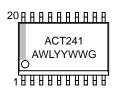
# ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS

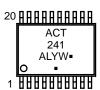


SOIC-20W DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E







A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol		Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5  to  +7.0	V
VI	DC Input Voltage		$-0.5 \le V_{I} \le V_{CC} + 0.5$	V
Vo	DC Output Voltage (Note 1)		$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I <sub>IK</sub>	DC Input Diode Current		±20	mA
I <sub>OK</sub>	DC Output Diode Current		±50	mA
Ι <sub>Ο</sub>	DC Output Sink/Source Current		±50	mA
I <sub>CC</sub>	DC Supply Current per Output Pin		±50	mA
I <sub>GND</sub>	DC Ground Current per Output Pin		± 100	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction temperature under Bias		+ 150	°C
$\theta_{JA}$	Thermal Resistance	SOIC TSSOP	96 128	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 > 1000	V
I <sub>Latchup</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 5)	± 100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I<sub>O</sub> absolute maximum rating must be observed.

2. Tested to EIA/JESD22–A114–A.

- Tested to EIA/JESD22-A115-A.
   Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

# RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
V <sub>CC</sub>	DC Input Voltage (Referenced to GND)	4.5		5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0		V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-40	25	+85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Note 7) $ V_{CC} = 4.5 \text{ V} $ $ V_{CC} = 5.5 \text{ V} $	0	10 8.0	10 8.0	ns/V
I <sub>OH</sub>	Output Current – High	_	_	-24	mA
I <sub>OL</sub>	Output Current – Low	_	_	24	mA

<sup>6.</sup> Unused Inputs may not be left open. All inputs must be tied to a high voltage level or low logic voltage level.
7. V<sub>in</sub> from 0.8 V to 2.0 V; refer to individual Data Sheets for devices that differ from the typical input rise and fall times.

#### **DC CHARACTERISTICS**

		V	T <sub>A</sub> = -	+25°C	T <sub>A</sub> = -40°C to +85°C		
Symbol	Parameter	V <sub>CC</sub> (V)	Тур	Gı	uaranteed Limits	Unit	Conditions
V <sub>IH</sub>	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V V	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V
V <sub>IL</sub>	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V V	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V
V <sub>OH</sub>	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V V	I <sub>OUT</sub> = -50 μA
		4.5 5.5	-	3.86 4.86	3.76 4.76	V V	$^{*}V_{IN} = V_{IL} \text{ or } V_{IH} -24 \text{ mA}$ $^{I}OH -24 \text{ mA}$
V <sub>OL</sub>	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V V	I <sub>OUT</sub> = 50 μA
		4.5 5.5	_	0.36 0.36	0.44 0.44	V V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ 24 mA $I_{OL}$ 24 mA
I <sub>IN</sub>	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$ , GND
$\Delta I_{CCT}$	Additional Maximum I <sub>CC</sub> /Input	5.5	0.6	-	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
I <sub>OZ</sub>	Maximum 3–State Current	5.5	-	±0.5	±5.0	μΑ	$ \begin{array}{c} V_{I}\left(OE\right) = V_{IL},V_{IH} \\ V_{I} = V_{CC},GND \\ V_{O} = V_{CC},GND \end{array} $
I <sub>OLD</sub> I <sub>OHD</sub>	†Minimum Dynamic Output Current	5.5 5.5	_	-	75 –75	mA mA	V <sub>OLD</sub> = 1.65 V Max V <sub>OHD</sub> = 3.85 V Min
I <sub>CC</sub>	Maximum Quiescent Supply Current	5.5	_	8.0	80	μΑ	$V_{IN} = V_{CC}$ or GND

<sup>\*</sup>All outputs loaded; thresholds on input associated with output under test.

# **AC CHARACTERISTICS** $t_r = t_f = 3.0$ ns (For Figures and Waveforms, See Figures 2, 3, and 4.)

		V*	T <sub>A</sub> = +25°C C <sub>L</sub> = 50 pF		$T_A = -40$ °C to +85°C $C_L = 50$ pF			
Symbol	Parameter	V <sub>CC</sub> *	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub>	Propagation Delay Data to Output	5.0	1.5	6.5	9.0	1.5	10.0	ns
t <sub>PHL</sub>	Propagation Delay Data to Output	5.0	1.5	7.0	9.0	1.5	10.0	ns
t <sub>PZH</sub>	Output Enable Time	5.0	1.5	6.0	9.0	1.0	10.0	ns
t <sub>PZL</sub>	Output Enable Time	5.0	1.5	7.0	10.0	1.5	11.0	ns
t <sub>PHZ</sub>	Output Disable Time	5.0	1.5	8.0	10.5	1.5	11.5	ns
t <sub>PLZ</sub>	Output Disable Time	5.0	2.0	7.0	10.5	1.5	11.5	ns

<sup>\*</sup>Voltage Range 5.0 V is 5.0 V  $\pm$ 0.5 V

# **CAPACITANCE**

Symbol	Parameter	Value Typ	Unit	Test Conditions
C <sub>IN</sub>	Input Capacitance	4.5	pF	V <sub>CC</sub> = 5.0 V
C <sub>PD</sub>	Power Dissipation Capacitance	45	pF	V <sub>CC</sub> = 5.0 V

<sup>†</sup>Maximum test duration 2.0 ms, one output loaded at a time.

# **SWITCHING WAVEFORMS**

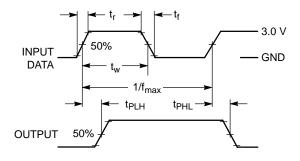


Figure 2.

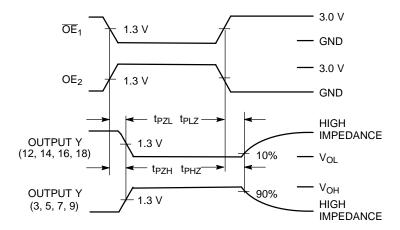
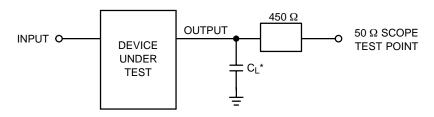


Figure 3.



\*Includes all probe and jig capacitance

Figure 4. Test Circuit

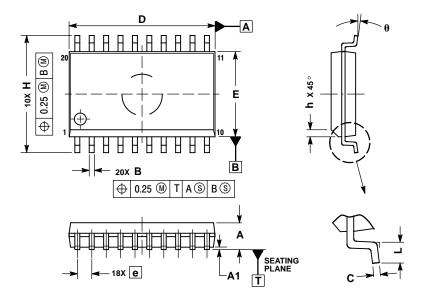
# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
MC74ACT241DW	SOIC-20		
MC74ACT241DWG	SOIC-20 (Pb-Free)	38 Units / Rail	
MC74ACT241DWR2	SOIC-20		
MC74ACT241DWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel	
MC74ACT241DTR2	TSSOP-20*	0500 (T 0 D l	
MC74ACT241DTR2G	TSSOP-20*	2500 / Tape & Reel	
MC74ACT241MEL	SOEIAJ-20		
MC74ACT241MELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*These packages are inherently Pb–Free.

# **PACKAGE DIMENSIONS**

SOIC-20W **DW SUFFIX** CASE 751D-05 **ISSUE G** 

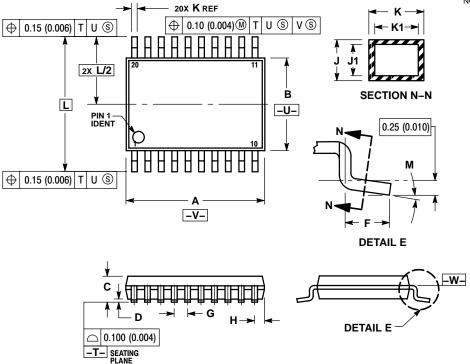


- NOTES:
  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS					
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.10	0.25				
В	0.35	0.49				
С	0.23	0.32				
D	12.65	12.95				
E	7.40	7.60				
е	1.27	BSC				
Н	10.05	10.55				
h	0.25	0.75				
L	0.50	0.90				
θ	0°	7 °				

#### PACKAGE DIMENSIONS

### TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE C**



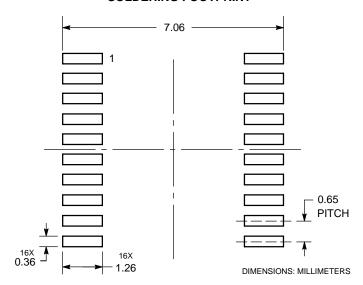
- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  - ANSI Y14.5M, 1982.
    2. CONTROLLING DIMENSION:
    MILLIMETER.
    3. DIMENSION A DOES NOT INCLUDE
    MOLD FLASH, PROTRUSIONS OR GATE
    BURRS. MOLD FLASH OR GATE BURRS
    SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
    4. DIMENSION B DOES NOT INCLUDE
    INTERLEAD FLASH OR PROTRUSION.
    INTERLEAD FLASH OR PROTRUSION
    SHALL NOT EXCEED 0.25 (0.01) PER SIDE.

  - SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
  - CONDITION.
    6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
    7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252	BSC	
М	00	80	n٥	80	

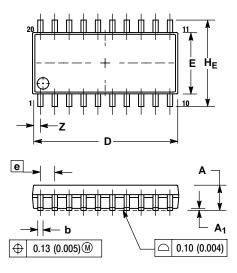
### **SOLDERING FOOTPRINT\***

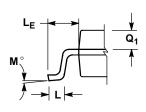


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

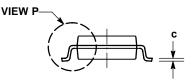
#### PACKAGE DIMENSIONS

#### SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE A**





**DETAIL P** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE
- MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  . TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIN	IETERS	TERS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05	-	0.081	
A <sub>1</sub>	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
С	0.15	0.25	0.006	0.010	
D	12.35	12.80	0.486	0.504	
Е	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050 BSC		
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
М	0 °	10°	0°	10°	
Q <sub>1</sub>	0.70	0.90	0.028	0.035	
Z		0.81		0.032	

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative